

## **Application Note**

Temperature Sensing using TrenchPLUS devices

**AN10137**

## Temperature Sensing using TrenchPLUS devices

### *Principle of using temperature sensors within Automotive applications.*

As the automotive industry moves towards driving higher power motors within (Electronic Powered Assisted Steering) EPAS or (Integrated Starter Alternator) ISA applications, the need for accurate temperature and current sensing becomes paramount.

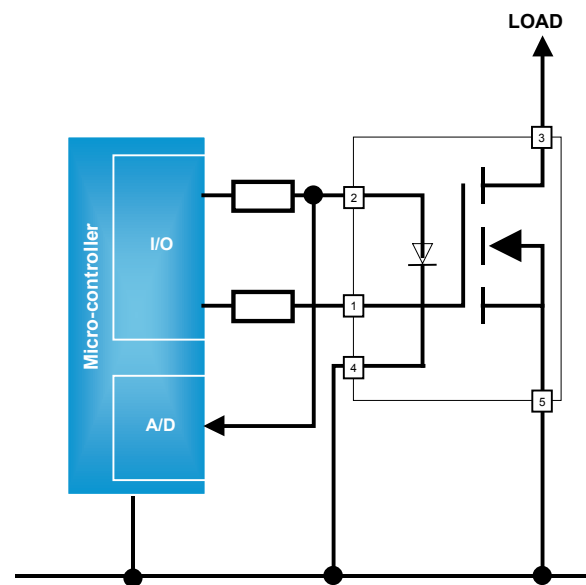
This application note considers some of the protection strategies available using Philips TrenchPLUS temperature sense devices.

The BUK9107-40ATC is an n-channel power MOSFET with *monolithically integrated* temperature sense and clamping diodes. This allows temperature sensing of the actual MOSFET chip. Designed for high current applications, the device has a typical  $R_{DS(ON)}$  of  $5.8\text{m}\Omega$  at  $25^\circ\text{C}$ , 5V gate drive, the market leader in its field.

### *Application example for Temperature Sensor*

It is relatively simple to incorporate temperature sensing into your protection strategy. Traditionally the addition of a comparator and a few passive components would allow a direct measure of the chip temperature and a means by which to protect your system. In this paper we would like to demonstrate that by using a suitable micro-controller, a more accurate method of control can be achieved.

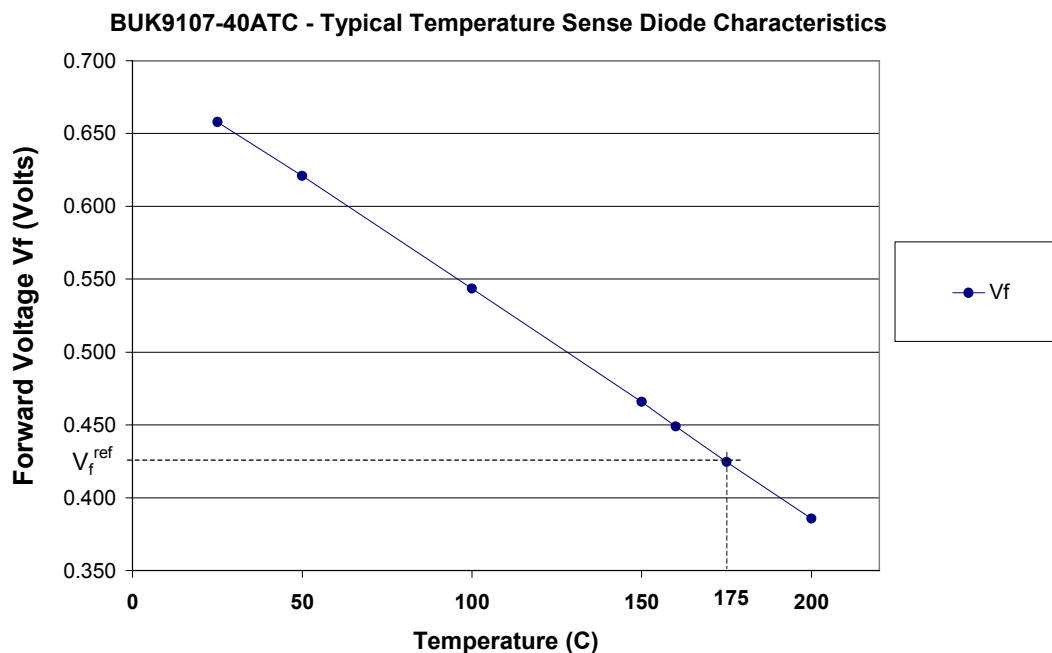
A typical circuit is shown in Figure 1. The MOSFET is shown on the right, being controlled by a micro-controller having an A/D input from the temperature sensor. The resistor values define the current in the sense diode – and hence its  $V_f$  - and gate switching time.



**Figure 1 - Typical Temperature Sense Circuit**

In normal operation, the  $V_f$  of the diode is monitored, and a reference voltage chosen below which the device turns off,  $V_f^{ref}$ . The value of  $V_f^{ref}$  chosen depends on  $S_f$  - the temperature coefficient of  $V_f$  - and the temperature at which the MOSFET should be switched off. The  $V_f$  characteristic is linear over the full temperature range – as shown in Figure 2 – thus enabling numerous protection strategies to be implemented. By continually monitoring  $V_f$  the micro-controller can provide early warning of over-temperature conditions, as well as determining the rate of change of temperature.

Furthermore, depending on the chosen micro it is possible to respond to the information provided by the temperature sensor in a variety of ways. The signals could be used to trigger a latched shutdown, shutdown and cyclic retries, or simply used as a diagnostic tool for the application.

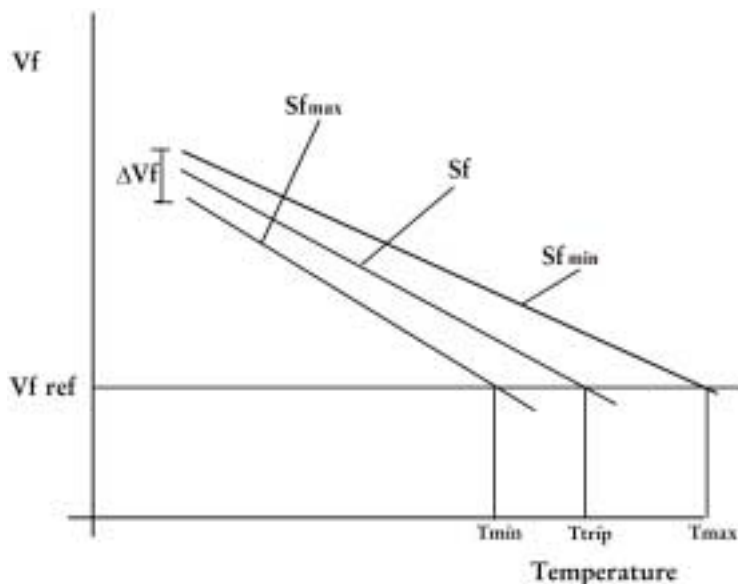


**Figure 2 - The variation of  $V_f$  with temperature for the temperature sense diode**

### ***Theoretical Estimate of device Accuracy***

The theoretical accuracy of the temperature sensor is dependent on three factors:-

- The uncertainty in the forward voltage,  $V_f$
- The uncertainty in the value of the temperature coefficient,  $S_f$
- The choice of reference voltage,  $V_f^{ref}$



**Figure 3: The variation of  $T_{trip}$  with changes in  $V_f$ ,  $S_f$ .**

Figure 3 demonstrates the effect of these factors more clearly. Any inherent variability in  $V_f$  will add a fixed offset to  $T_{trip}$ . Variations in the temperature coefficient are shown by a change in the gradient. A lower  $S_f$  will cause the device to trip at a higher temperature,  $T_{max}$ . Depending on the trip temperature this could lead to devices operating above their maximum operating temperature, which would be detrimental to their lifetime. Conversely, a higher temperature coefficient would lead to erroneous nuisance tripping below the desired set point. Both these factors have implications on the protection strategy employed.

The total error is the sum of the contributions from the uncertainty in both  $V_f$  and  $S_f$ .

Table 1 shows the datasheet values for the temperature sense diode.

	MIN	TYPICAL	MAX
$V_f$ (mV)	648	658	668
$S_f$ (mV/K)	1.40	1.54	1.68

**Table 1 - Temp Sense Diode Characteristics**

The BUK9107-40ATC has a very tight  $V_f$  tolerance of  $\pm 10$ mV and the variation in  $S_f$  is correspondingly tight too. However, if the device were used in the circuit of Figure 1 without calibration then the total error in the trip temperature due to the errors in both  $V_f$  and  $S_f$  becomes significant.

The maximum error will occur if the  $V_f$  ( $25^\circ\text{C}$ ) is at its highest and  $S_f$  is low.

If the trip temperature were set to 150°C, then the error in  $T_{trip}$  is given by

$$T_{Trip} = \frac{(V_f - \overline{V_f^{ref}})}{S_f} - (T_{Trip} - 25)$$

**Equation 1 - Trip temperature if neither Vf, nor Sf are measured**

where the average reference voltage,  $\overline{V_f^{ref}} = \overline{V_f} - (T_{Trip} - 25) \times \overline{S_f} = 465.5mV$ .

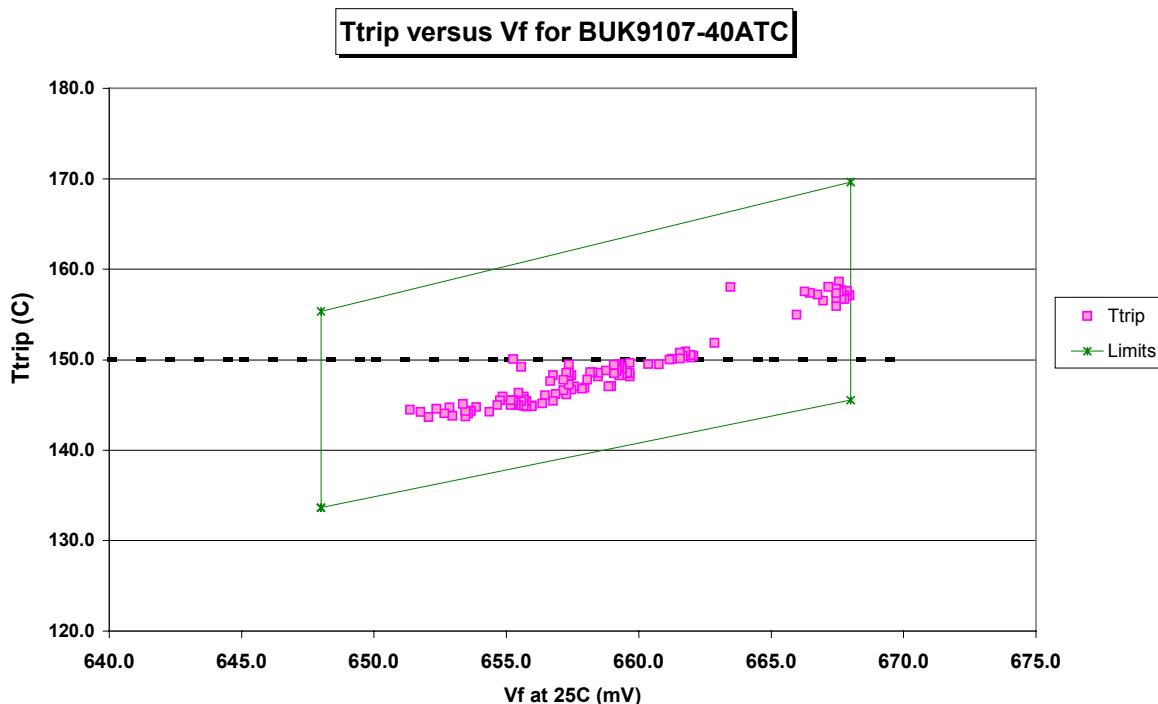
Substituting the datasheet values into the above equations yields

$$T_{Max} = 150 + 19.6^\circ C$$

$$T_{Min} = 150 - 16.4^\circ C$$

In practice the results are much better than this.

A number of devices have been measured across the temperature range and the actual trip temperature determined for each using a reference voltage of 465.5mV. A plot of trip temperature versus  $V_f$  measured at 25°C is shown below.

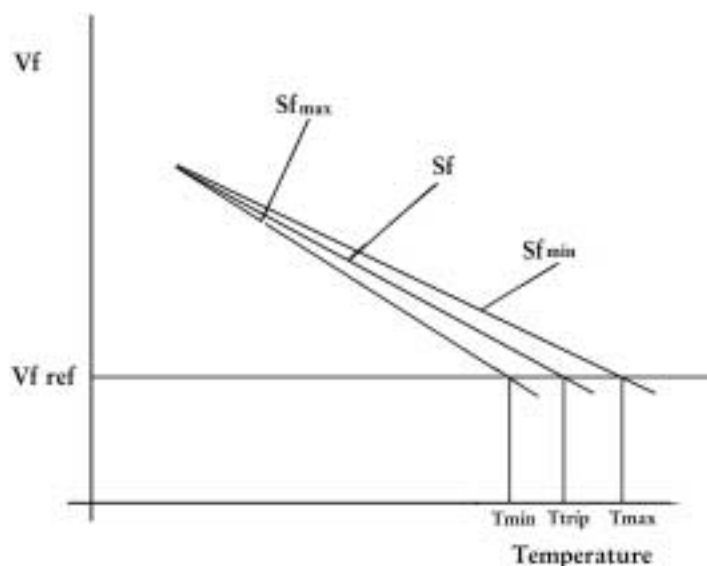


**Figure 4 - Measured Trip temperature as a function of Vf without making any corrections.**

The box defines the theoretical limits of the trip temperature. It is clear that the data lies within  $\pm 10^\circ\text{C}$  of the target temperature.

### **Improving the accuracy**

The accuracy of the device can be vastly improved if a measure is made of the room temperature value of  $V_f$ . Using this value,  $V_f^{ref}$  can be reset to eliminate the error in  $V_f$ . This situation is visualised in Figure 5:



**Figure 5 - If  $V_f$  is measured, the error in  $T_{trip}$  will decrease.**

In this case there is still an error associated with  $S_f$ , shown by the variation in gradient. As before the max/min values of  $S_f$  are taken from the datasheet (Table 1).

The error is now given by the expression,

$$d(\Delta T) = -\Delta V_f \frac{dS_f}{(S_f)^2} + \frac{1}{S_f} d(\Delta V_f)$$

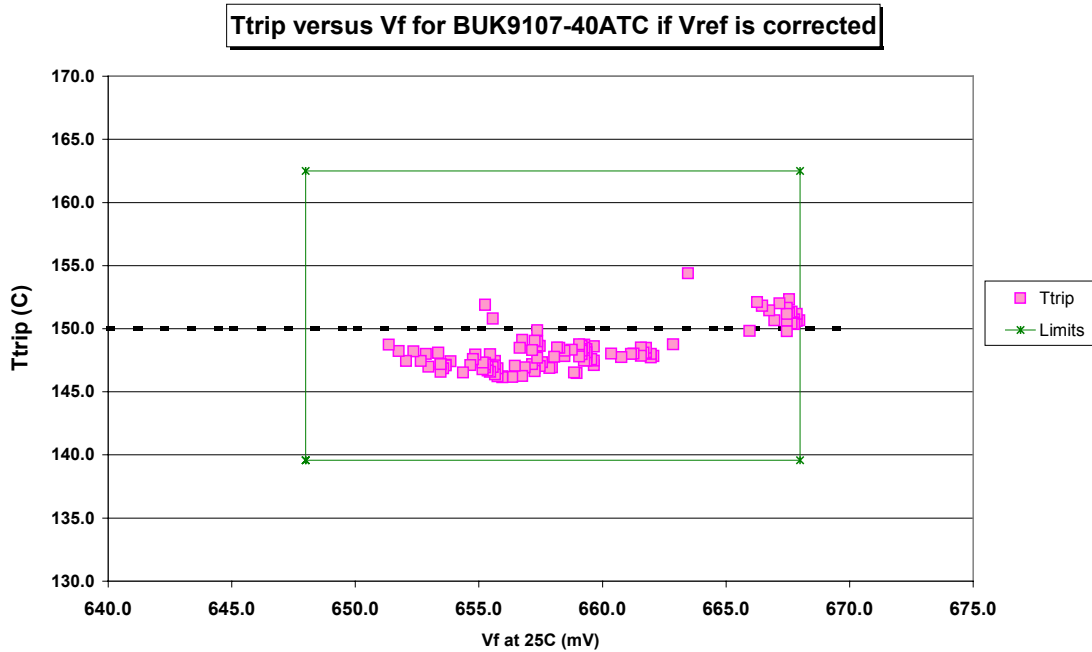
### **Equation 2 – Total error in trip point**

where  $\Delta V_f$  is the voltage drop required to trip at  $150^\circ\text{C}$  from  $25^\circ\text{C}$ , and  $dS_f$  is the variation in the temperature coefficient given in the datasheet ( $1.68 - 1.54 = 0.14$ ). By adjusting the reference voltage the term on the right hand side of Equation 2 becomes zero. Substituting the remaining values yields,

$$T_{trip} = 150 \pm 11^\circ\text{C}$$

Again actual results are better than this.

An estimate of the actual trip temperature was made for the same devices using an adjusted reference voltage,  $V_f^{ref}$ , the results of which are shown in Figure 3.



**Figure 3 - Measured trip temperature if reference voltage adjusted**

As before the outer box defines the theoretical limit, which has now become  $T_{trip} = 150 \pm 11^\circ\text{C}$ . The measured values now lie within  $\pm 5^\circ\text{C}$  of the target. It is clear that significant improvements in accuracy are possible from a simple measure of the room temperature  $V_f$ .

A further theoretical improvement can be made because a relationship exists between  $S_f$  and  $V_f$  measured at  $25^\circ\text{C}$ . The accuracy will be increased if  $V_f(25^\circ\text{C})$  is measured, and  $S_f$  calculated using the expression given in Equation 3.

Using the graph, if  $V_f(25^\circ\text{C})$  is measured the value of  $S_f$  will lie in the range

$$S_{f_{calc}} = \{[-0.0041 \times Vf(25C)] + 4.2387\} \pm 0.099$$

**Equation 3 – Empirical definition of  $S_f$  from  $V_f$  measured at  $25^\circ\text{C}$ .**

The 0.099 error in  $S_f$  represents 5 standard deviations from the mean. If we again assume that the trip temperature,  $T_{trip}$ , is set to  $150^\circ\text{C}$ , the accuracy now becomes

$$T_{trip} = 150 \pm 8^\circ\text{C}$$



Of course, the greatest accuracy is achieved if both  $V_f$  and  $S_f$  are measured for each device. In this case  $V_f$  (25°C) and  $V_f$  (150°C) are measured, and  $S_f$  is calculated and stored using

$$S_f = \frac{V_f(25) - V_f(150)}{150 - 25}.$$

Again,  $V_f^{ref}$  must be redefined as in method two. In this way the trip temperature will be limited only by the accuracy of the voltmeter used, and an accuracy of  $\pm 1^\circ\text{C}$  can be readily achieved. This could be integrated in to the module build to provide excellent temperature control in your system.

**Summary**

There are 4 methods of using the temperature sense diode each with increasing theoretical accuracy. The 2 simplest methods have been measured and compared with theory. A summary of results is shown here

	Theory	Experiment
No Measure of $V_f$	$T_{trip} = 150 \pm 19^\circ\text{C}$	$T_{trip} = 150 \pm 10^\circ\text{C}$
Measure $V_f$ (25C), and use $S_f = 1.40 - 1.68$	$T_{trip} = 150 \pm 11^\circ\text{C}$	$T_{trip} = 150 \pm 5^\circ\text{C}$
Measure $V_f$ (25C), and calculate $S_f$	$T_{trip} = 150 \pm 8^\circ\text{C}$	
Measure $V_f$ and $S_f$	$T_{trip} = 150 \pm 1^\circ\text{C}$	